

N-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV _{DSS} /	R _{DS(ON)} (max)	I _{D(ON)}	Order Number / Package		
BV _{DGS}		(min)	TO-92		
60V	7.5Ω	0.75A	VN2222LL		

Features

- □ Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- □ Low C_{ISS} and fast switching speeds
- Excellent thermal stability
- □ Integral Source-Drain diode
- □ High input impedance and high gain
- Complementary N- and P-channel devices

Applications

- Motor controls
- Converters
- Amplifiers
- Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

Absolute Maximum Ratings

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV _{DGS}
Gate-to-Source Voltage	± 30V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

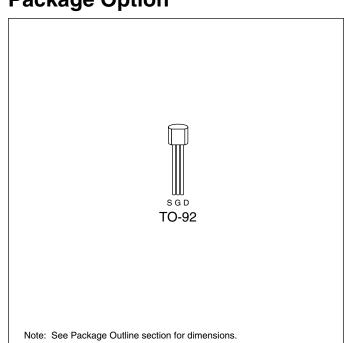
* Distance of 1.6 mm from case for 10 seconds.

Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Option



11/12/01

Supertex Inc. does not recommend the use of its products in life support applications and will not knowingly sell its products for use in such applications unless it receives an adequate "products liability indemnification insurance agreement." Supertex does not assume responsibility for use of devices described and limits its liability to the replacement of devices determined to be defective due to workmanship. No responsibility is assumed for possible omissions or inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications, refer to the Supertex website: http://www.supertex.com. For complete liability information on all Supertex products, refer to the most current databook or to the Legal/Disclaimer page on the Supertex website.

Thermal Characteristics

Package	I _D (continuous)*	I _D (pulsed)	Power Dissipation @ T _C = 25°C	θ _{jc} °C/W	θ _{ja} °C/W	I _{DR} *	I _{DRM}
TO-92	0.23A	1.0A	1W	125	170	0.23A	1.0A

* I_{D} (continuous) is limited by max rated T_{i} .

Electrical Characteristics (@ 25°C unless otherwise specified)

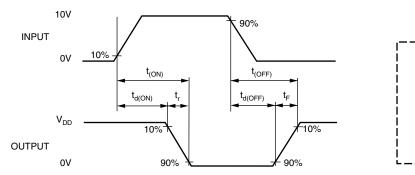
Symbol	Parameter	Min	Тур	Max	Unit	Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	60			V	$V_{GS} = 0V, I_{D} = 100 \mu A$	
V _{GS(th)}	Gate Threshold Voltage	0.6		2.5	V	$V_{GS} = V_{DS}, I_D = 1mA$	
I _{GSS}	Gate Body Leakage			100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
I _{DSS}	Zero Gate Voltage Drain Current			10		$V_{GS} = 0V, V_{DS} = Max Rating$	
				500	μΑ	$V_{GS} = 0V, V_{DS} = 48V$ $T_A = 125^{\circ}C$	
I _{D(ON)}	ON-State Drain Current	0.75			Α	$V_{GS} = 10V, V_{DS} = 10V$	
R _{DS(ON)}	Static Drain-to-Source ON-State Resistance			7.5	Ω	$V_{GS} = 5V, I_D = 0.2A$	
				7.5	Ω	V _{GS} = 10V, I _D = 0.5A	
G _{FS}	Forward Transconductance	100			mប	$V_{DS} = 10V, I_{D} = 0.5A$	
C _{ISS}	Input Capacitance			60			
C _{OSS}	Common Source Output Capacitance			25	pF	$V_{GS} = 0V, V_{DS} = 25V$ f = 1 MHz	
C _{RSS}	Reverse Transfer Capacitance			8			
t _(ON)	Turn-ON Time			10	20	$V_{DD} = 15V, I_D = 0.6A$ $R_{GEN} = 25\Omega$	
t _(OFF)	Turn-OFF Time			10	ns		
V _{SD}	Diode Forward Voltage Drop		0.85		V	$V_{GS} = 0V, I_{SD} = 0.2A$	

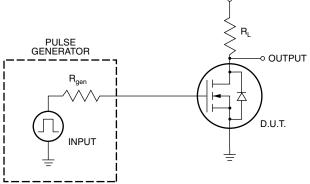
Notes:

1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)

2. All A.C. parameters sample tested.

Switching Waveforms and Test Circuit





 V_{DD}